電子電路設計模擬與實習

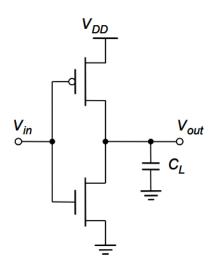
實驗名稱:CMOS 反向器延遲時間分析

班級:電子二乙

組員: U0922113 郭晏寧

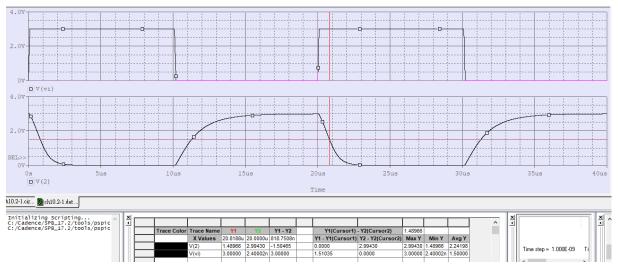
U0922107 張志斌

Lab 10-2. CMOS 反向器延遲時間分析實驗電路圖:

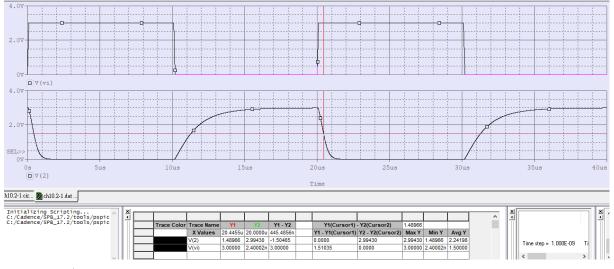


1. NMOS W/L 尺寸與 t_{pHL} 之關係

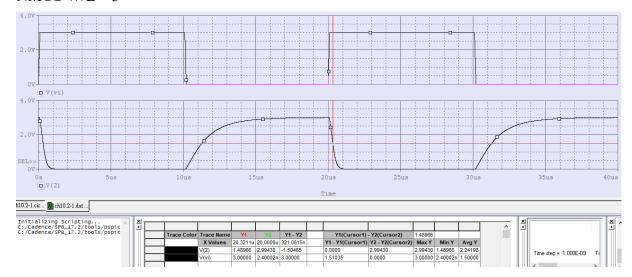
t_{pHL}	NMOS W/L (L=0.18μm)			
	1.5	3	4. 5	
PMOS W/L=3	1OS W/L=3 0. 8188μ		0.3211μ	



NMOS W/L = 1.5



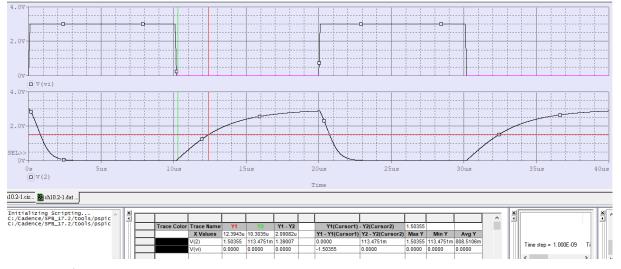
NMOS W/L = 3



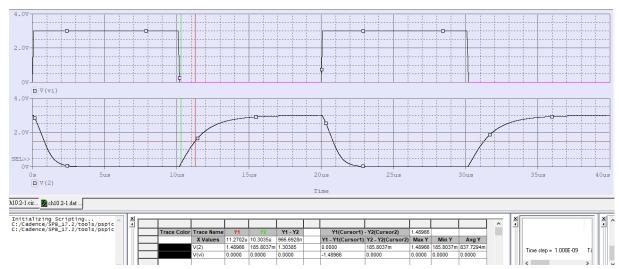
NMOS W/L = 4.5

2. PMOS W/L 尺寸與 t_{pLH} 之關係

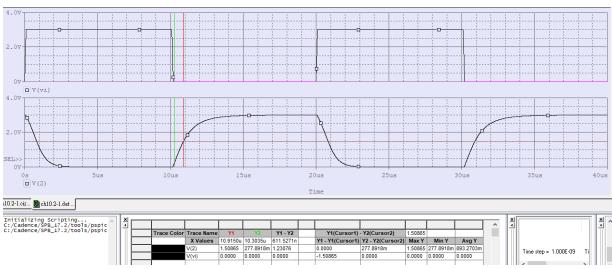
t	PMOS W/L (L=0.18um)			
t_{pLH}	1.5	3	4. 5	
PMOS W/L=3	2.0908μ	0.9667μ	0.6115μ	



PMOS W/L = 1.5



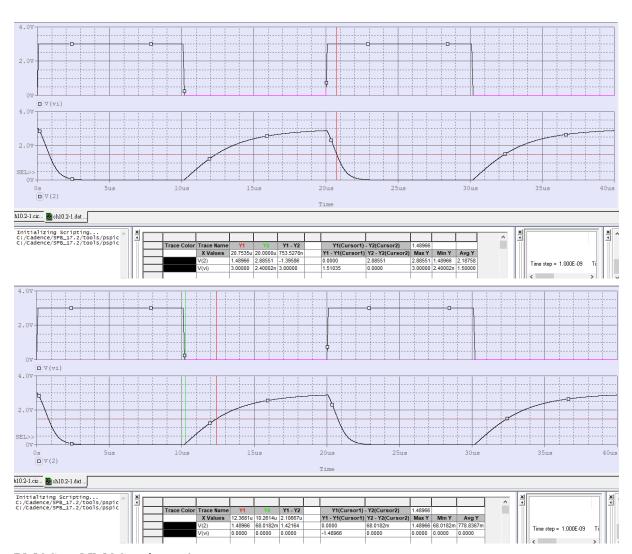
PMOS W/L = 3



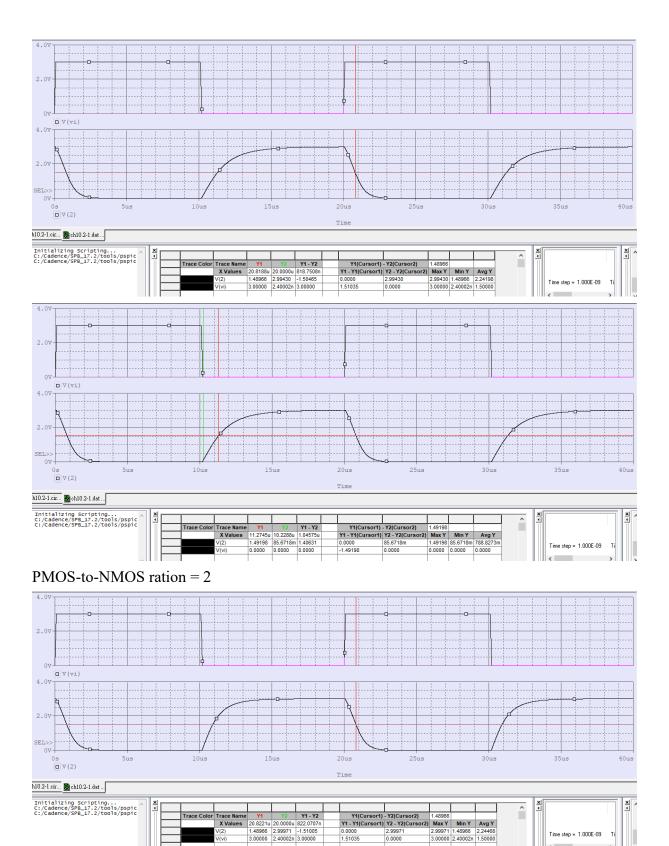
PMOS W/L = 4.5

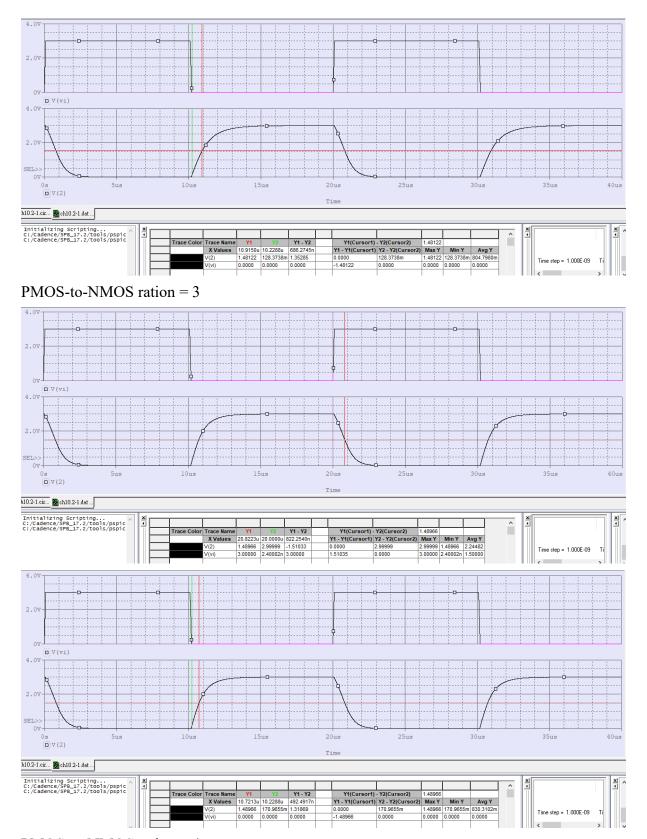
3. PMOS、NMOS W/L 的尺寸比(PMOS-to-NMOS ration)與 t_{pHL} 、 t_{pLH} 之關係

	PMOS-to-NMOS ration (L=0.18um)				
	1	2	3	4	5
t_{pHL}	0.7535μ	0.8188μ	0.8221μ	0.8223μ	0.8223μ
t_{pLH}	2.1067μ	1.0457μ	0.6862μ	0.4925μ	0.35μ

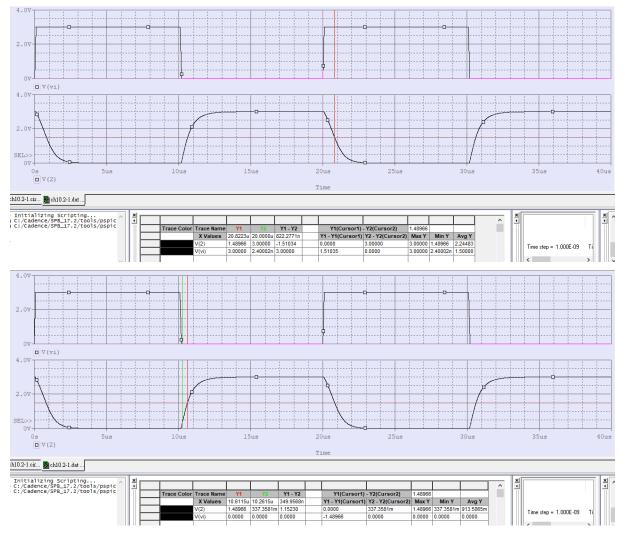


PMOS-to-NMOS ration = 1





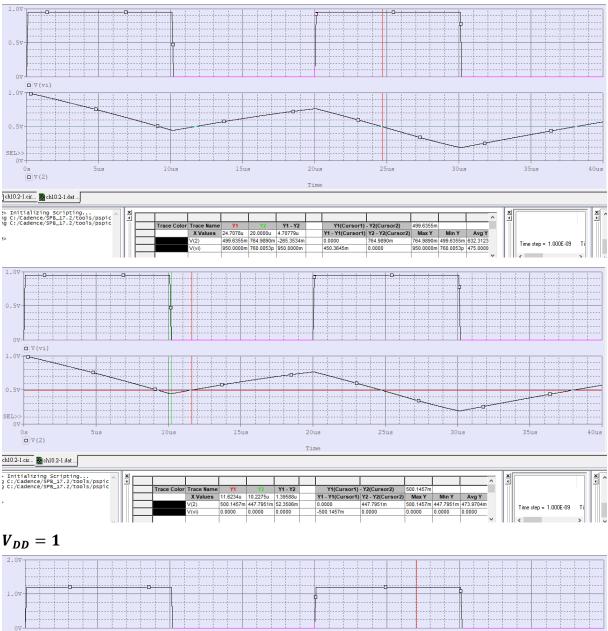
PMOS-to-NMOS ration = 4

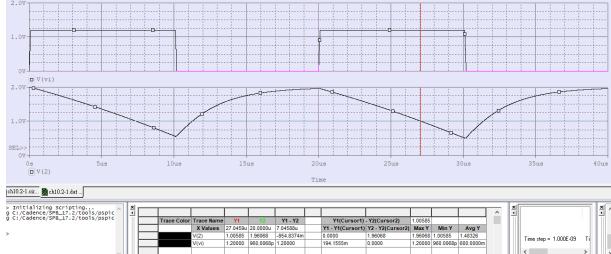


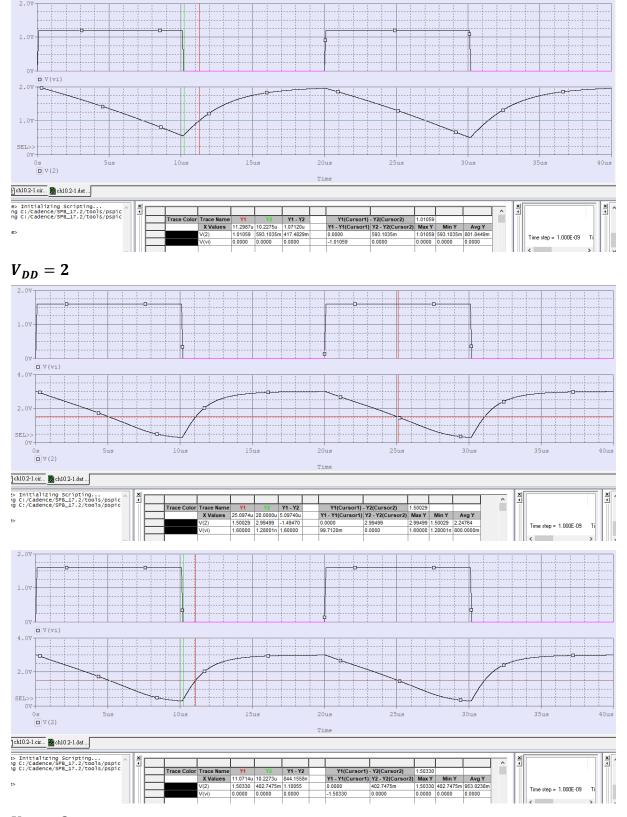
PMOS-to-NMOS ration = 5

4. 電源電壓 V_{DD} 與 t_{pHL} 、 t_{pLH} 之關係。(NMOS W/L=1.5 及 PMOS W/L=3 (L=0. 18um))

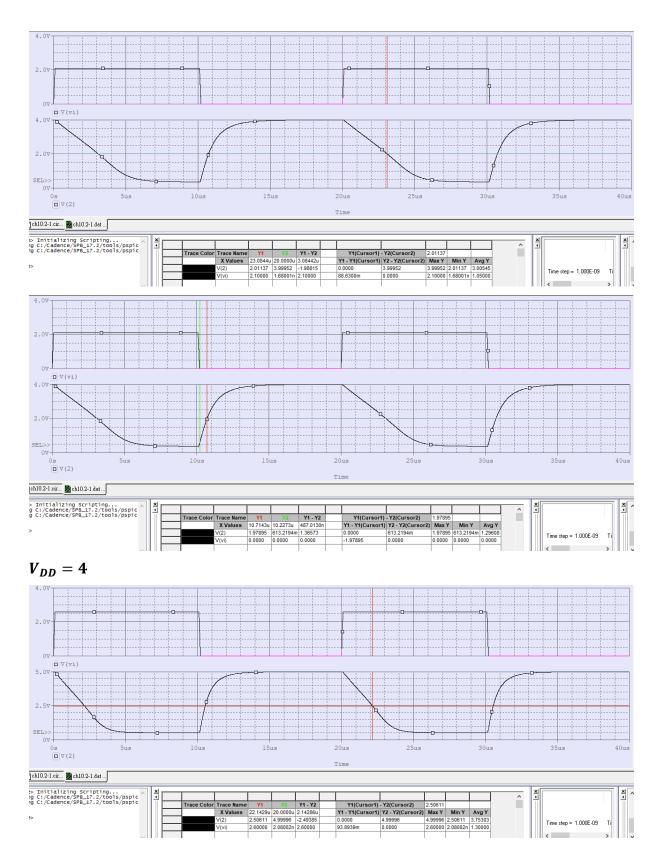
	V_{DD}				
	1	2	3	4	5
t_{pHL}	4.7078μ	7.0459µ	5.0974μ	3.0844μ	2.1429μ
t_{pLH}	1.3959μ	1.0712μ	0.8441μ	0.487μ	0.3119μ

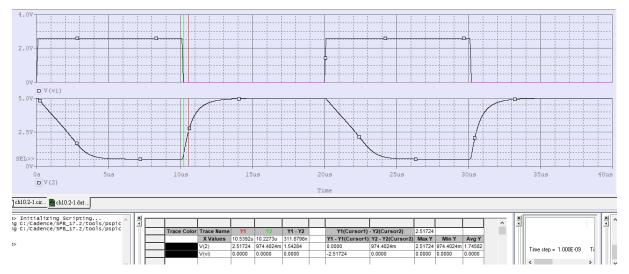






 $V_{DD}=3$

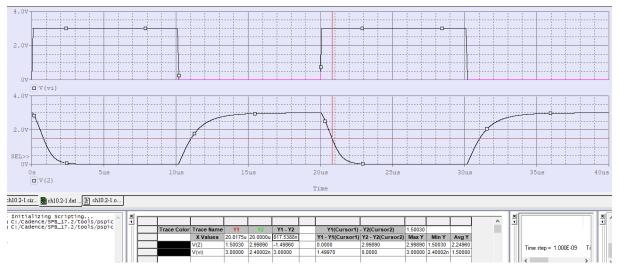




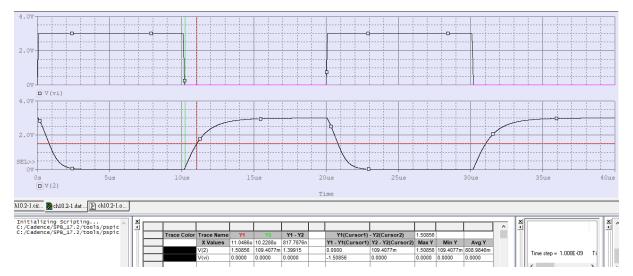
 $V_{DD} = 5$

5. 設計 (決定 PMOS、NMOS W/L 的尺寸比) $-t_{pHL}$ 、 t_{pLH} 相同之 CMOS 反向器 (假設 L = 0.18um, V_{DD} = 3V)

NMOS : L = 0.18um , W = 0.27um 。 PMOS : L = 0.18um , W = 0.69um 。



 $t_{pHL} = 817.5388ns$



 $t_{pLH} = 817.7876$ ns